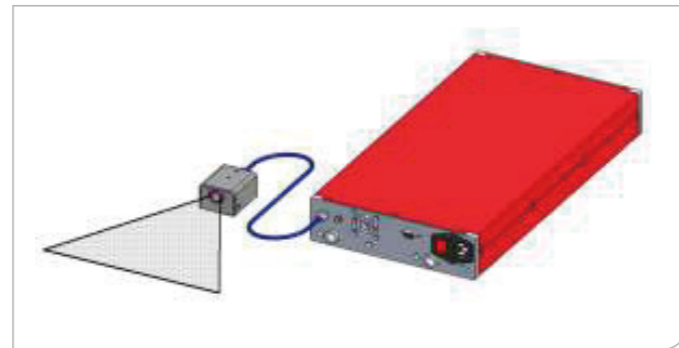
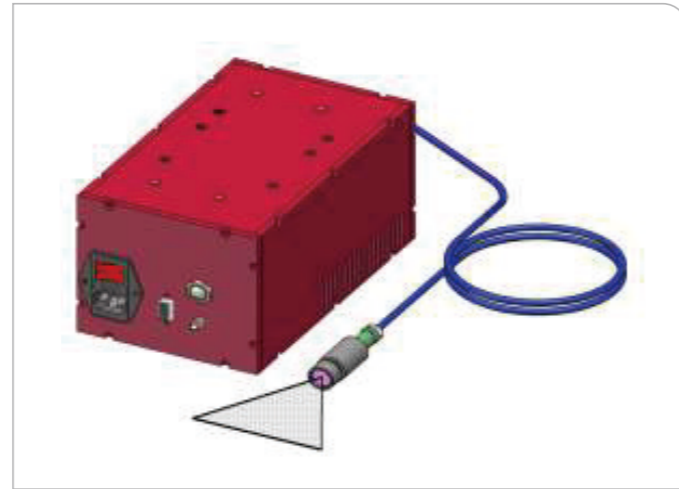
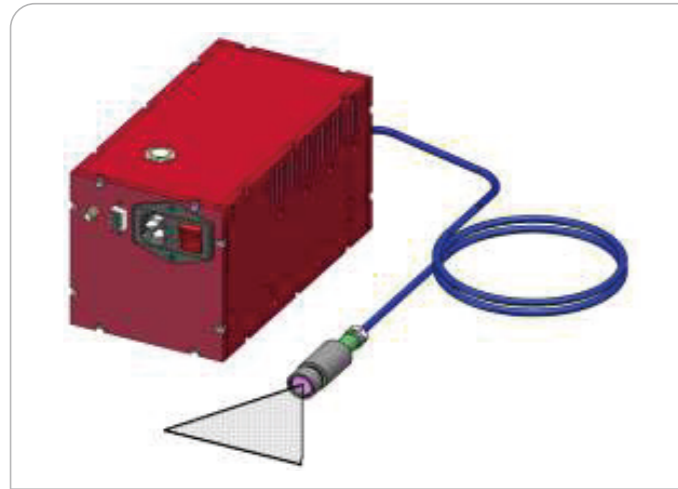


Diode Laser 30/50/200W

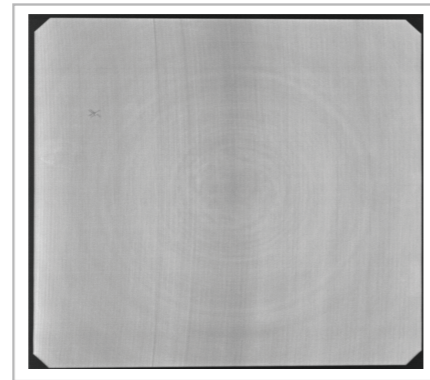


Application Advantages

- Output power can be customized according to specific needs
- High beam uniformity is conducive to fluorescence imaging capturing by cameras
- Different laser lenses can be configured according to different working distances
- Software-controlled beam emission enables enhanced versatility in laser applications



JPT-30W/50W
Camera capture diagram



JPT-200W
Camera capture diagram

Specifications

Parameter	Unit	Parameter		
Product Model		JPT-30W	JPT-50W	JPT-200W
Output Power	W	30	50	200
Central Wavelength	nm	808		915
Center Wavelength Deviation		±5		±10
Typical Working Distance	mm	230~260		
Detectable Wafer Size	mm	≤230		
Power Requirements	V	220		
IO Interface	V	White 0~24+/ Black 0~0.5-		
Average Power Consumption	W	100	130	560
Beam Emission Control		IO Interface		
Power Regulation Mode		GUI		
Operating Temp.&Rh	°C	20~30; <80%		
Dimension	mm	205×111×123	232×140×122	450×235×70
Weight	kg	≈4	≈5	≈10
Applicable Technology		Process After Silicon Wafer Coating	Process After Silicon Wafer Diffusion	Subsequent Processes of Silicon Wafers
Cooling		Air-Cooled		Water-Cooled